

Silicon NPN Power Transistors

2SC4369

DESCRIPTION

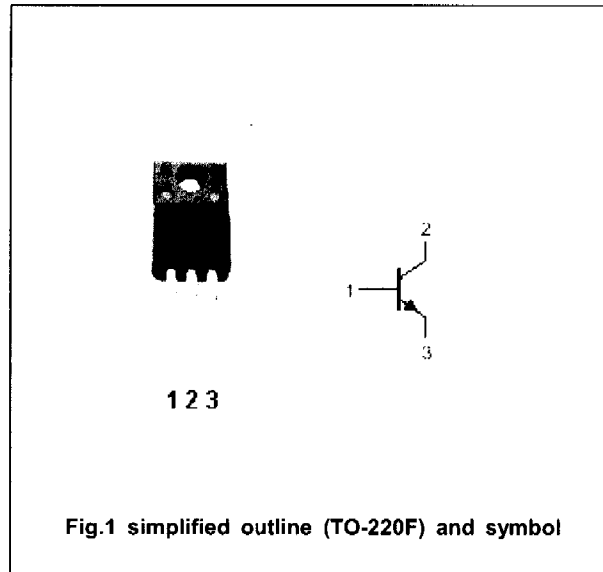
- With TO-220F package
- Complement to type 2SA1658
- Good linearity of h_{FE}

APPLICATIONS

- For general purpose applications

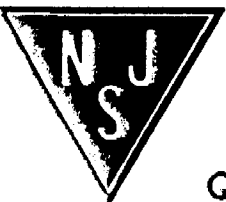
PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings ($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	30	V
V_{CEO}	Collector-emitter voltage	Open base	30	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		3	A
I_B	Base current		0.3	A
P_C	Collector dissipation	$T_c=25^\circ$	15	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	



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CHARACTERISTICS

T_J=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	30			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A ; I _E =0.2A			0.8	V
V _{BE}	Base-emitter on voltage	I _C =0.5A ; V _{CE} =2V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =20V ; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			1.0	μA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =2V	70		240	
h _{FE-2}	DC current gain	I _C =2.5A ; V _{CE} =2V	25			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =2V		100		MHz

◆ h_{FE-1} Classifications

O	Y
70-140	120-240